L Number	Hits	Search Text	DB	Time stamp
1	79113	LSI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 09:51
2	22650	LSI and (integrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 09:51
3	22650	"LSI" and (integrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 09:51
4	2373	"LSI" and (integrated adj circuit) and expansion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 09:52
5	951	"LSI" and (integrated adj circuit) and (thermal adj expansion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 09:53
6	115	("LSI" adj circuit) and (thermal adj expansion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 09:55
7	96	("LSI" adj circuit) and (thermal adj expansion) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 09:59
8	22	("LSI" adj circuit) and substrate and ((aluminum adj oxide) or (platinum NEAR doped))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:08
9	0	("LSI" adj circuit) and (substrate NEAR2 ((aluminum adj oxide) or (platinum NEAR doped)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:08
10	22	("LSI" adj circuit) and substrate and ((aluminum adj oxide) or (platinum NEAR doped))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:12
11	0	("LSI" adj circuit) and (substrate NEAR ((aluminum adj oxide) or (platinum)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:12
12	4	("LSI" adj circuit) and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:16

13	231	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:16
14	196	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum))) and (metal or plastic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:17
15	19	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum))) and (metal and plastic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:17
16	1	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) and (platinum))) and (metal and plastic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:17
17	1	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) and (platinum))) and (metal or plastic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:18
18	196	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum))) and (metal or plastic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:20
19	657	(integrated adj circuit) and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum))) and (metal or plastic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:20
20	5	(integrated adj circuit) and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum))) and ((metal or plastic) NEAR circuit$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:25
21	703	(integrated adj circuit) and (substrate NEAR ((aluminum adj oxide) or ("SiO.sub.2"))) or ((platinum adj doped) adj (silicon adj wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:26
22	0	(integrated adj circuit) and (substrate NEAR ((aluminum adj oxide) or ("SiO.sub.2"))) and ((platinum adj doped) adj (silicon adj wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:26
23	702	(integrated adj circuit) and (substrate NEAR ((aluminum adj oxide) or ("SiO.sub.2"))) or ((platinum adj doped) adj (silicon adj wafer)) and ("LSI")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:26
24	702	(integrated adj circuit) and (substrate NEAR ((aluminum adj oxide) or ("SiO.sub.2"))) or ((platinum adj doped) adj (silicon adj wafer)) and ("LSI") and metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:27

25	89	(integrated adj circuit) and (substrate NEAR ((aluminum adj oxide) or ("SiO.sub.2"))) and ("LSI") and metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:27
26	0	(integrated adj circuit) and ((platinum adj doped) adj (silicon adj wafer)) and ("LSI") and metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:27
27	0	((platinum adj doped) adj (silicon adj wafer)) and ("LSI") and metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:27
28	1	((platinum adj doped) adj (silicon adj wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:27
29	13	((platinum) adj (silicon adj wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:28
30	2	((platinum) adj (silicon adj wafer)) and (integrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:36
31	1220	"LSI" and (integrated adj circuit) and metal and plastic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:36
32	960	"LSI" and (integrated adj circuit) and metal and plastic and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:37
33	3	"LSI" and (integrated adj circuit) and metal and plastic and (substrate NEAR ((aluminum adj oxide) or platinum))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:37